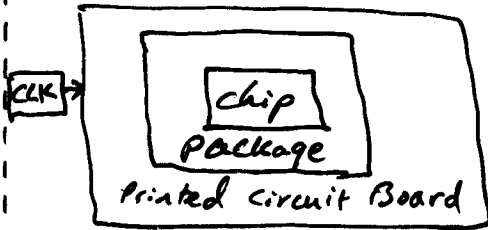


CHAPTER 11 - POWER GRID AND CLOCK DESIGN

DEAL WITH HOW TO DISTRIBUTE VDD, GND, AND CLK TO VARIOUS POINTS ON THE CHIP

POWER DISTRIBUTION DESIGN



Problems:

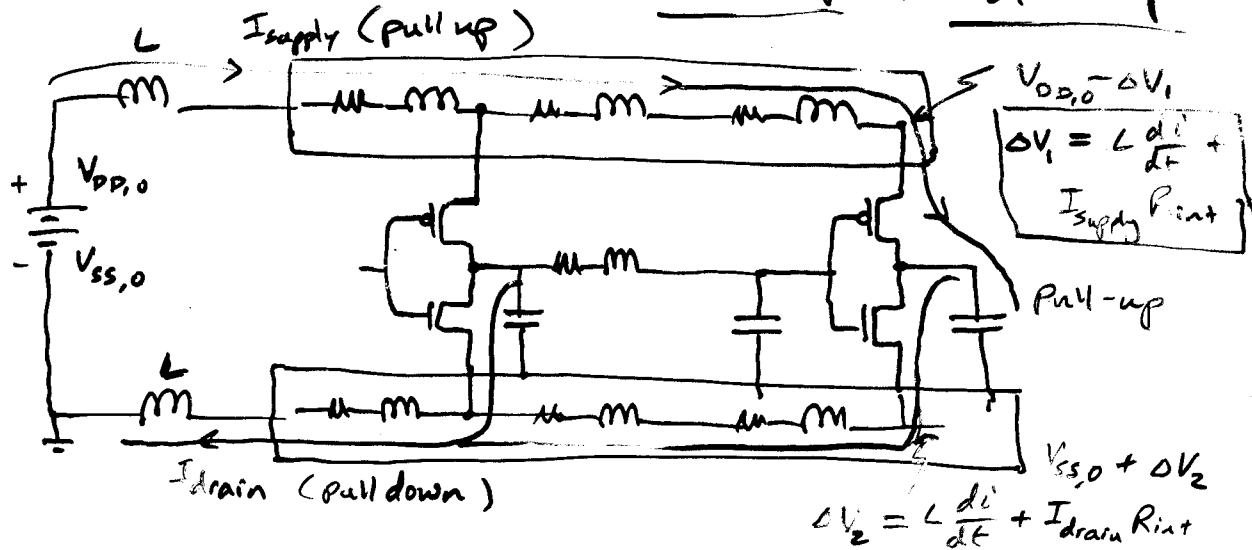
- 1) CLK frequency ↑
- 2) Current ↑
- 3) Power ↑
- 4) # of Transistors ↑

According to 2003 ITRS (public.itrs.net)

Year	nd #	Vdd	CLK	AMP
Year 2004	90 nm	1.2 V	~4 GHz	158 Watts
Year 2018	18 nm	0.7 V	~53 GHz	300 Watts

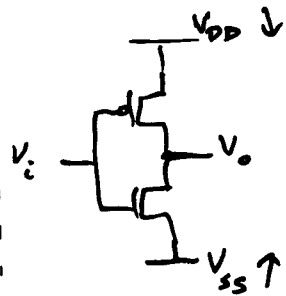
$AL \rightarrow C_u \Rightarrow R \downarrow$ } $\Rightarrow RC \text{ delay} \rightarrow LC \text{ delay}$
 $0.18 \mu m \quad 0.13 \mu m \quad CLK \uparrow$

Illustration of IR drop & $L \frac{di}{dt}$ drop



Worst case : Far end of Line node
 & Simultaneous Switching

To see the effects of IR drop and $L \frac{di}{dt}$ drop let's revisit the inverter (ref. Fig. 4.12 P.68)



First observation:

IR and $L \frac{di}{dt}$ drop cause

$V_{DD} \downarrow$ and $V_{SS} \uparrow$

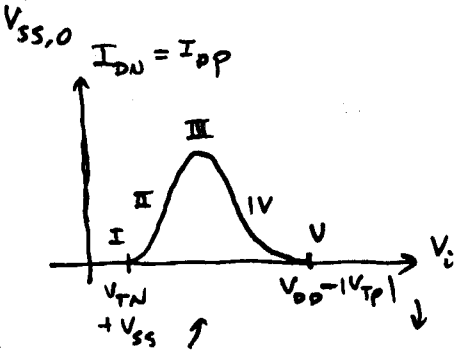
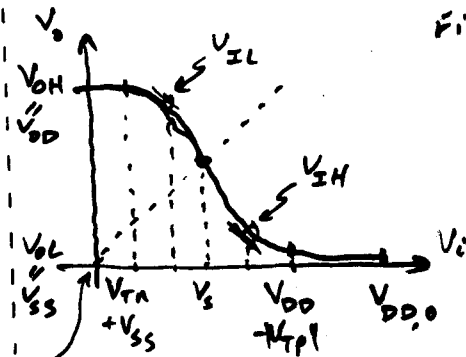
so what?

First response: Power \downarrow OK.

$$NM_H = V_{OH} \downarrow - V_{IH} \uparrow \quad \downarrow \downarrow$$

$$NM_L = V_{IL} \downarrow - V_{OL} \uparrow \quad \downarrow \downarrow$$

Reliability worse!



If $V_{DD} - |V_{TP}| \downarrow$

$V_{TN} + V_{SS} \uparrow$

then we see III will disappear

i.e. no region where both nmos and pmos in sat.

\Rightarrow gain \downarrow

\Rightarrow Regeneration \downarrow (Noise)

Roughly, $V_{DD} - V_{SS} \geq 2V_T = 2 \frac{kT}{q} \approx 50 \text{ mV}$ to sustain a gain > 1

Yet, another interesting thing will happen:

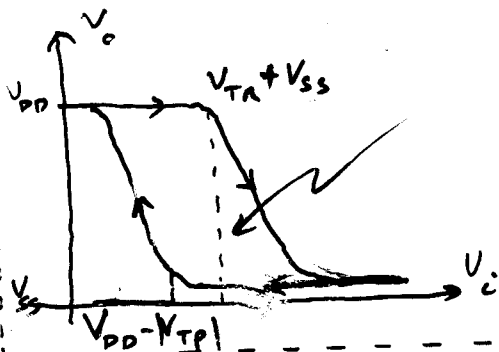
HYSTERESIS!

i.e. V_i has no control

over V_o !

When $V_{TN} + V_{SS} > V_{DD} - |V_{TP}|$

i.e. $V_{DD} - V_{SS} < V_{TN} + |V_{TP}|$



Electromigration:

At high current levels, metal molecules will migrate and can result in SHORT or OPEN circuits.

Measuring metric: Mean-time-to-failure = MTTF

$$MTTF = \frac{A}{J^2} \exp\left(\frac{\Delta H}{KT}\right) \propto \frac{1}{J^2}$$

where $J = \frac{I_{avg}}{W \cdot T}$ = average dc current density

Power Supply Routing:

1) \wedge IR drop.

$$R = \frac{\rho L}{A} \frac{1}{W}$$

no control vertically

have control horizontally

$\Rightarrow \downarrow L \quad \uparrow W$

To reduce

use Cu instead of Al $\Rightarrow \downarrow \rho$
and less aggressively scale down T

2) \wedge $L \frac{di}{dt}$

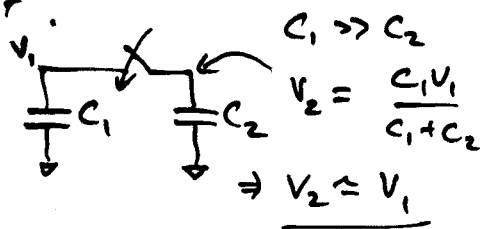
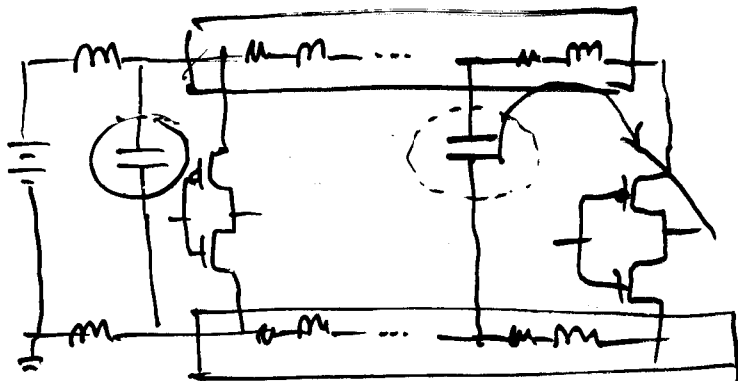
Keep Line short

To reduce

don't run lines in parallel w/ current
in the same direction (mutual Ind.)

Decoupling Capacitance Design

Big Capacitance to ground helps to hold the interconnect potentials constant.



CLOCK AND TIMING ISSUES

Clock Definitions and metrics

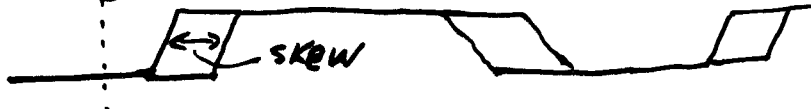
Ideal clock :



clock with finite
risetime and delay
Falltime (latency)

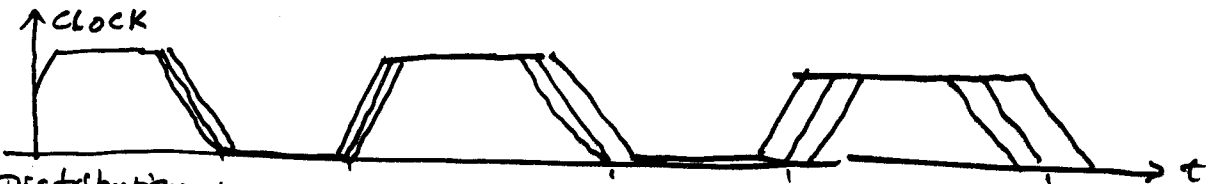


clock with finite
rise/fall-time, latency

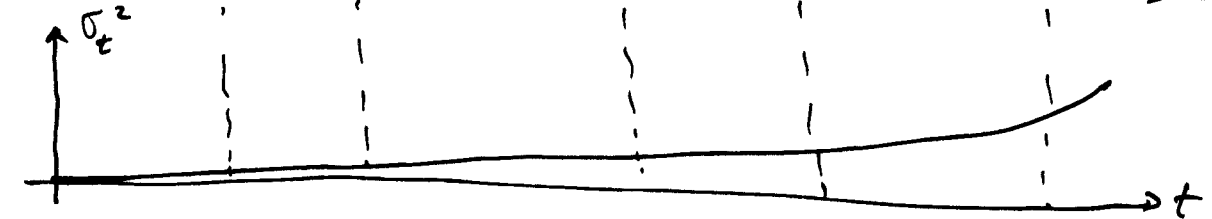
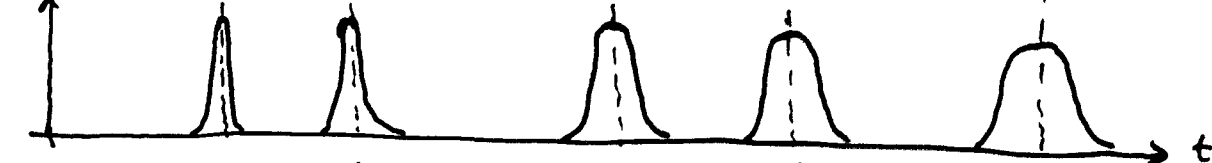


and skew (SAME clock, at DIFFERENT locations)
edge

Clock jitter (time domain, at SAME POINT)



Distribution
of Deviation



σ_t^2 = variance

Short-time jitter : $\sigma_t \propto \sqrt{t}$

Long-time jitter : $\sigma_t \propto t$

Accumulative effect
of the timing uncertainty